VERSION WITH MARKINGS TO SHOW CHANGES MADE

7. (Amended) A process for underfilling an integrated circuit that is mounted to a substrate, comprising:

dispensing a first [underfill] material acting as underfill which becomes attached to the integrated circuit and the substrate; and,

dispensing a second [underfill] material [which becomes attached to the integrated circuit and the substrate] acting as underfill, the second material having a lower adhesive property than the first material.

8. (Twice Amended) The process as recited in claim [11]7, wherein the first [underfill] material flows between the integrated circuit and the substrate.

9. (Twice Amended) The process as recited in claim 8, wherein the substrate moves within an oven while the first [underfill] material flows between the integrated circuit and the substrate.

10. (Twice Amended) The process as recited in claim [11]7, wherein the second [underfill] material is dispensed in a pattern which surrounds the first [underfill] material.

11. (Twice Amended) A process for underfilling an integrated circuit that is mounted to a substrate comprising:

heating the substrate before a first [underfill] material is dispensed;

dispensing the first [underfill] material [which becomes] acting as underfill, the first material becoming attached to the integrated circuit and the substrate; and,

dispensing a second [underfill] material [which become] acting as a circumferential fillet, the second material having a lower adhesion property than the first material and becoming attached to the integrated circuit and the substrate.

12. (Twice Amended) The process as recited in claim 11, further comprising heating the first [underfill] material to a [partial] gel state.

13. (Twice Amended) The process as recited in claim 12, wherein the substrate is heated to a temperature that is greater than a temperature for heating said first [underfill] material to said partially gel state.

14. (Twice Amended) The process as recited in claim 11, further comprising mounting the integrated circuit to the substrate with a solder bump before the first [underfill] material is dispensed.

15. (Cancel)

16. (Cancel)

17. (Cancel)

18. (Cancel)

19. (Cancel)

20. (Cancel)

21. (Cancel)

22. (Cancel)

23. (Cancel)

24. (Cancel)

25. (Cancel)

26. (New) An integrated circuit package comprising:

a substrate;

an integrated circuit attached to the substrate;

a first material placed between the substrate and the integrated circuit as underfill; and

a second material placed around edges of the integrated circuit and the first material to act as a circumferential fillet, the second material having a lower adhesion property than the first material.

27. (New) The integrated circuit of claim 26, wherein the second material is an anhydride epoxy.

28. (New) The integrated circuit of claim 26, wherein the substrate is baked at a temperature greater than a temperature at which the first and second materials are applied.

29. (New) The integrated circuit of claim 26, wherein the second material seals the first material.

30 . (New) The integrated circuit of claim 26, wherein the second material is applied at a temperature less than a temperature at which the first material is applied.

APPENDIX A

Shin-Etsu

Shin-Etsu Chemical Co., Ltd.
6-1, Ohtemachi 2-chome, Chiyoda-ku, Tokyo 100-0004, Japan

Fax sending form			April 16, 2002
To:	Blakely Sokoloff Taylor & Zafman Mr. William W. Schaal	From:	Electronics Materials Division Organic Electronics Materials Department Yamakawa Tel:81-3-3246-5231 Fax:81-3-3246-5367
Cc:	 Tel: Fax: +1-714-557-3347		Total: 6 pages (including this page)

Semicoat" product data

Dear Sir

Please receive the requested information of "Semicoat" product.
I have enclosed the requested product data and general information of "Semicoat".
5230JP is underfill and 122X is fillet forming material.

Best Regards,
Yamakawa

PAP. NO. 8 ATTACHMENT

Product data sheet

Shin-Etsu

Grade		SEMICOAT5230JP	SEMICOAT122X
Feature		Exceptional good moisture resistance to prevent the delamination	Fillet forming to reinforce crack-resistance
Filler content	wt%	67.5	78.0
Filler Size (Max/Mean.)	micron	48/7	80/12
ITEM			
Appearance		Black	Black
Viscosity : 25C	Pa·s	280.0	35.0
Gelation Time : 145C	sec	410	63 at 150C
Flow Distance : 120C	mm	28	-
Specific Gravity		1.72	1.82
Glass Transition Temp.	C	140	155
CTE 1	ppm/C	25	15
CTE 2	ppm/C	76	65
Flexural Strength	N/mm2	98	118
Flexural Modulus	N/mm2	8200	12000
Volume resistively : 25C	TΩ m	more than 10	more than 10
Dielectric constant at 1KHz		3.7	3.5
Cure condition		120C*0.5hrs+150C*2hrs	120C*0.5hrs+150C*2hrs
Condition (Device temp.)		110-120C	-
Storage condition		below -40C	below -40C

SEMICOAT series

Shin-Etsu Chemical Co.,Ltd.